

Amendment

Clean Claims

11. (Twice Amended) A high holding voltage LVTSCR-like structure, comprising
an emitter,
a drain contact region, and
a floating drain, wherein the emitter is located so that at least part
of the drain contact region is located between a gate and the emitter.
12. (Twice Amended) A structure of claim 11, wherein the drain contact region is split into
at least one first drain portion located near the gate, and at least one second drain portion.
16. (Twice Amended) A structure of claim 12, wherein the floating drain and drain contact
region are separated by a shallow trench isolation region.